
Phenomenological Application of Target Theory Effects in SEE Analysis

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Section 514

The research in this report was carried out by The Jet Propulsion Laboratory, California Institute of Technology, under a contract with National Aeronautics and Space Administration.

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- **Complex biological cell systems and SEE vulnerable systems have similar traits**
- **SEE defined as atypical behavior in an irradiated system**
 - ◆ Microelectronic cells may upset from ion strike
 - ◆ Biological cells may suffer critical event far earlier than predicted
- **Target theory describes events as a smooth function of total dose**
 - ◆ SEU and early cell death should not be defined well by single hit target theory that is generally used
- **Target theory should be applied in a new way**

- **Target theory describes events in low LET environment**

- ◆ Irradiation must be mostly continuous and have complete coverage
- ◆ Cell or bit may not recover from radiation effect

$$\frac{dN}{dt} = -\frac{N}{C} \qquad N_s = N_0 e^{-\frac{t}{C}}$$

$$N_d = N_0 \left(1 - e^{-\frac{t}{C}} \right) \qquad F_{tt}(t) = \left(1 - e^{-\frac{t}{C}} \right)^D$$

- ◆ C and D determined partially by manufacturing parameters in microelectronics

- **For high LET systems, target theory will have a different coverage function, $g()$**
 - ◆ Discontinuous irradiation and variable coverage
 - ◆ Target recovery and TID Effects
- **Leading to:**

$$F_{tt}(0) = \left(1 - e^{-\frac{g(0)}{c}} \right)^D$$

$$g(\) = g(t, \dot{D}, T, \theta)$$

- ◆ or even

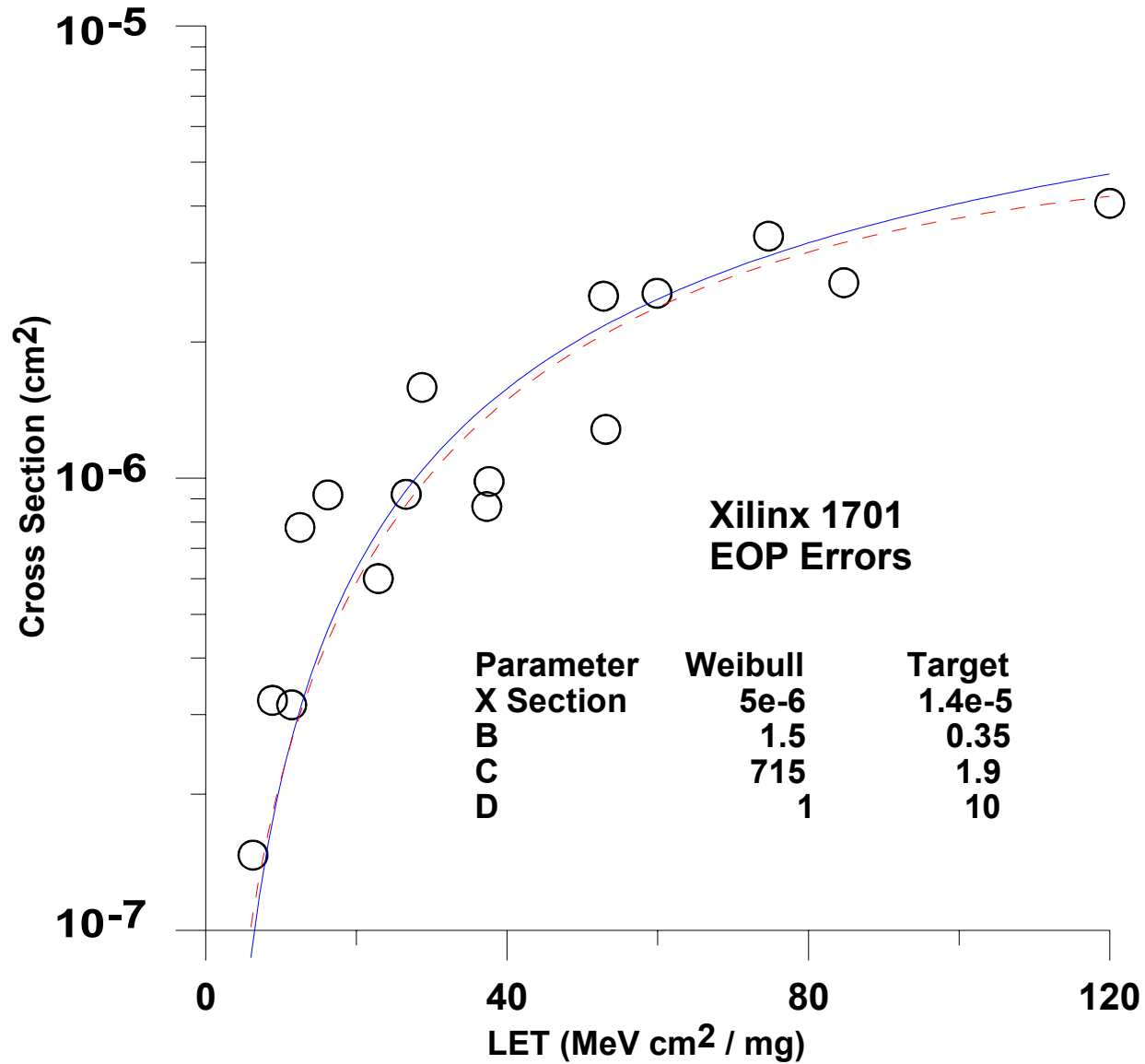
$$g(\) = g(t, \dot{D}, T, \theta, LET) \qquad D = D(t, LET)$$

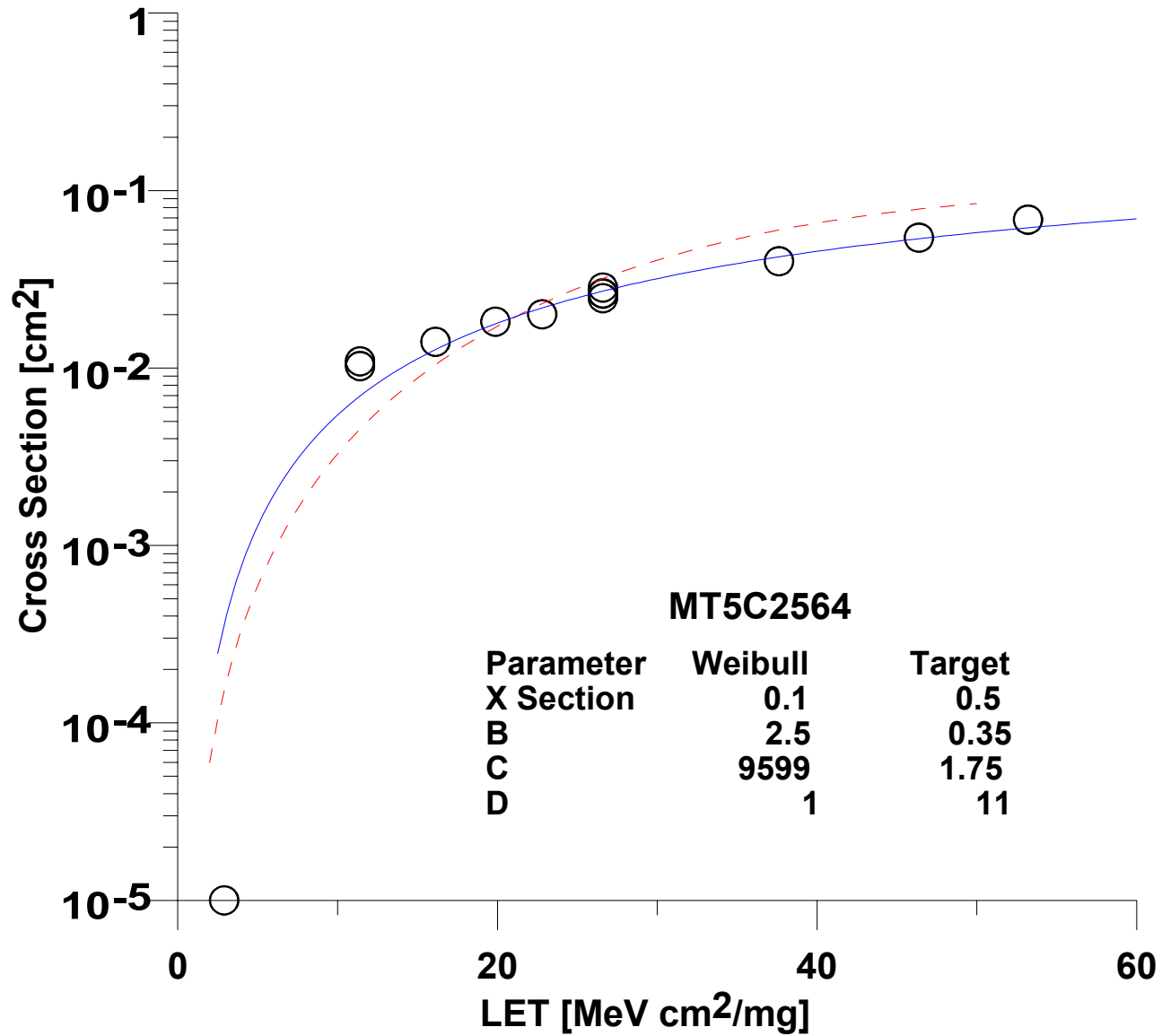
- **What could be the LET dependence?**
 - ◆ If LET and time are related, then the target theory analysis may explain SEU response.
 - ◆ Empirically, one can say that higher LET will have more effect:

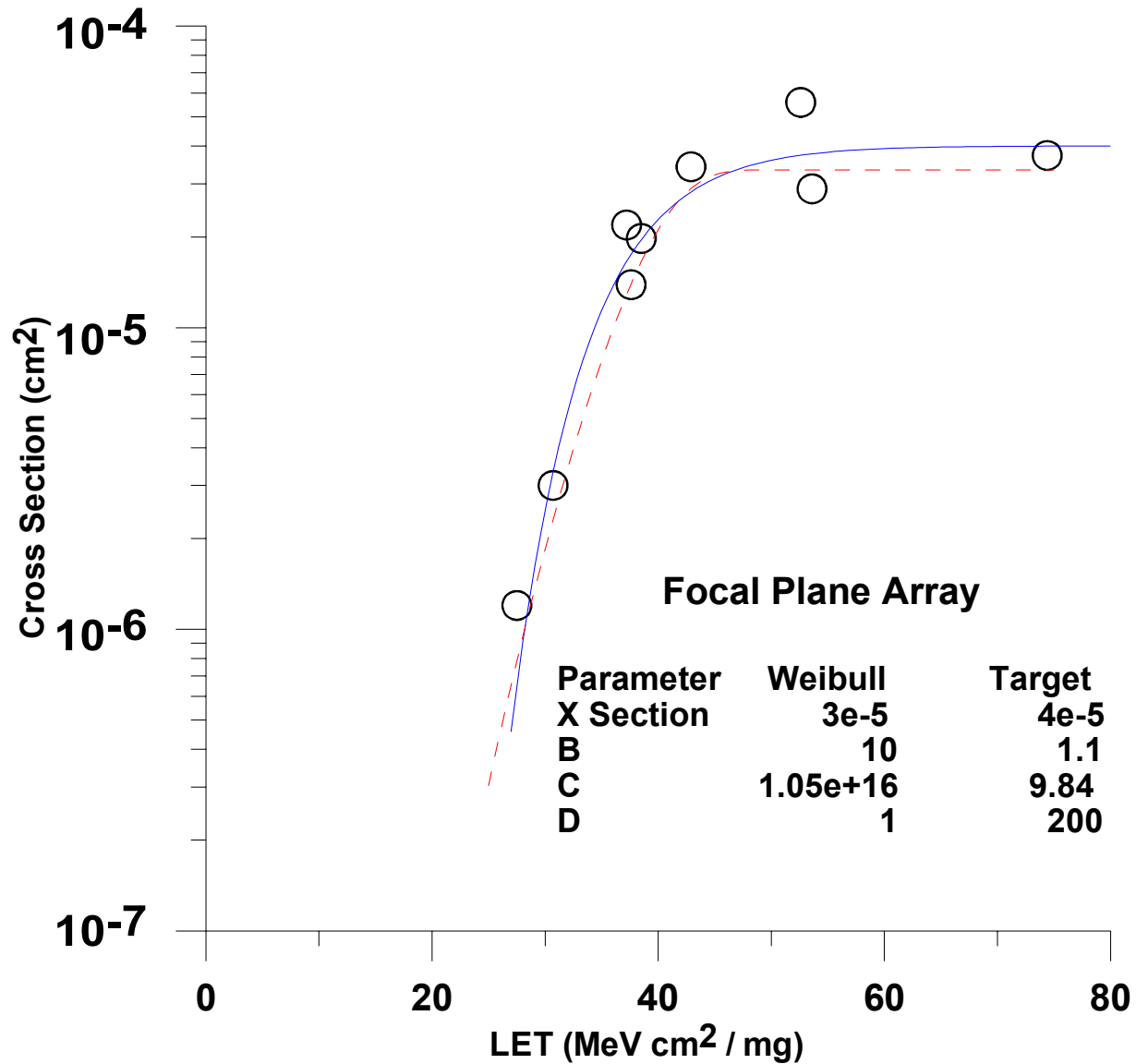
$$g(\) = LET^B$$

$$F_{tt}(LET) = \left(1 - e^{-\frac{LET^B}{C}} \right)^D$$

- **Much like the Weibull Or Bendel Curves**







- **What do the parameters mean?**
 - ◆ B is the Weibull shaping parameter
 - Production variable
 - ◆ C is a hybrid parameter
 - Related to the LET threshold of the device
 - B and C together determine the behavior at low LET
 - ◆ D is the target theory parameter
 - Determines the behavior at high LET
 - C and D together determine behavior at high LET
 - ◆ Correlates to sensitive volume
 - Complex function of B, C, D

- **Exact distribution must be known**
 - ◆ High precision required for low LET SEU prediction
- **Knowing parameters of the distribution allows for prediction of threshold events**
 - ◆ Analyses like Extreme Value theory are very dependent on distribution precision
- **Re-evaluate lifetimes of systems in inhomogeneous radiation environments**
 - ◆ Target theory can describe accrual of interface states concurrently with SEE effects

- **Threshold LET may give valuable insight to SEU dynamics**
 - ◆ Extrapolation to radiobiological application
- **Statistics of Microeffects**
 - ◆ Threshold LET measurements should allow sensitive volume measurements
 - ◆ Using D to get number of targets, C to get target threshold and B to get target distribution should reveal sensitive volume structure

- **Target theory analysis highly dependent on probabilistic charge collection by SEU sensitive regions**
 - ◆ Good Points
 - Three degrees of freedom in fitting SEU cross section curves
 - Can be extrapolated to hybrid TIP/SEE studies
 - ◆ Bad Points
 - Parameters convolute in any kind of fitting procedure
 - Approximations made in derivation dilute parameters
 - Does not predict maximum cross section